

L1: (3573) (257/700,703,705,707,782) CCLS.

L2: (749) (438/125) CCLS.

L3: (583) (219/121,71) CCLS.

L5: (12) 2 and (laser near5 weld\$3)

L6: (13) 3 and (laser near5 weld\$3)

L4: (31) 1 and (laser near5 weld\$3)

Failed

Saved

(2874) (257/700,703,705,707) CCLS.

(683) (438/125) CCLS.

(527) (219/121,71) CCLS.

(23178) laser near5 weld\$3

(11327) ceramic adj layer

(95992) metal adj layer

(0) (laser near5 weld\$3) with (ceramic adj layer) wi

(0) (laser near5 weld\$3) same (ceramic adj layer) se

(24) (laser near5 weld\$3) and (ceramic adj layer) ar

(4) ((laser near5 weld\$3) and (ceramic adj layer) an

(11) ((438/125) CCLS.) and (laser near5 weld\$3)

(10) ((219/121,71) CCLS.) and (laser near5 weld\$3)

		<input type="button" value="Browse"/>	<input type="button" value="Queue"/>	<input type="button" value="Clear"/>		
DBs:	USPAT, US_PPLUS, EPO, JPQ, DERWENT, IBM, TDB					
Default operator:		OR				
<input type="checkbox"/> Plurals <input type="checkbox"/> Highlight all but terms initially						
<input type="text" value="l and (laser near5 weld\$3)"/>						

U	I	Document ID	Issue Date	Pages	Title	Current	Cur	Re	Inventor	S	C	P	J
2	✓	US 20030178718 A1	20030925	8	Hermetically enhanced pl	257/701	257/		Ehly, Jonathan P. et al.	✓	✓	✓	✓
3	✓	US 6632028 B1	20031014	12	Apparatus and method fo	385/88	257/		Yang, Renyi et al.	✓	✓	✓	✓
4	✓	US 6507114 B2	20030114	12	BOC semiconductor pac	257/738	257/		Hui, Chong Chin et al.	✓	✓	✓	✓
5	✓	US 6404042 B1	20020611	16	Subcarrier and semicond	257/678	257/		Sone, Minoru et al.	✓	✓	✓	✓
6	✓	US 6316832 B1	20011113	28	Moldless semiconductor	257/747	257/		Tsuzuki, Koji et al.	✓	✓	✓	✓
7	✓	US 6166438 A	20001226	20	Ultrathin electronics usin	257/725	257/		Davidson, Howard	✓	✓	✓	✓

Ready

HTML